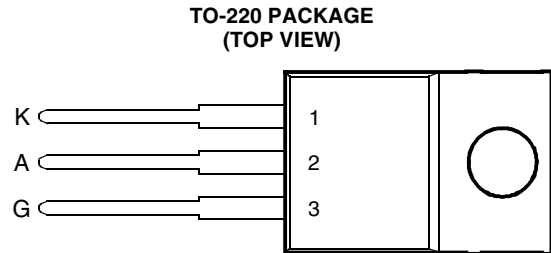


- 8 A Continuous On-State Current
- 80 A Surge-Current
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 20 mA



Pin 2 is in electrical contact with the mounting base.

MDC1ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---------|--------------|-------------|------|
| Repetitive peak off-state voltage | TIC116D | V_{DRM} | 400 | V |
| | TIC116M | | 600 | |
| | TIC116S | | 700 | |
| | TIC116N | | 800 | |
| Repetitive peak reverse voltage | TIC116D | V_{RRM} | 400 | V |
| | TIC116M | | 600 | |
| | TIC116S | | 700 | |
| | TIC116N | | 800 | |
| Continuous on-state current at (or below) 70°C case temperature (see Note 1) | | $I_{T(RMS)}$ | 8 | A |
| Average on-state current (180° conduction angle) at (or below) 70°C case temperature (see Note 2) | | $I_{T(AV)}$ | 5 | A |
| Surge on-state current at (or below) 25°C case temperature (see Note 3) | | I_{TM} | 80 | A |
| Peak positive gate current (pulse width $\leq 300 \mu s$) | | I_{GM} | 3 | A |
| Peak gate power dissipation (pulse width $\leq 300 \mu s$) | | P_{GM} | 5 | W |
| Average gate power dissipation (see Note 4) | | $P_{G(AV)}$ | 1 | W |
| Operating case temperature range | | T_C | -40 to +110 | °C |
| Storage temperature range | | T_{stg} | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | T_L | 230 | °C |

- NOTES: 1. These values apply for continuous dc operation with resistive load. Above 70°C derate linearly to zero at 110°C.
 2. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 70°C derate linearly to zero at 110°C.
 3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
 4. This value applies for a maximum averaging time of 20 ms.

PRODUCT INFORMATION

TIC116 SERIES SILICON CONTROLLED RECTIFIERS



electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|-----------|--|----------------------------------|---------------------|---------------------------------|-----|-----|-----|------------------|
| I_{DRM} | Repetitive peak off-state current | $V_D = \text{rated } V_{DRM}$ | | $T_C = 110^\circ\text{C}$ | | | 2 | mA |
| I_{RRM} | Repetitive peak reverse current | $V_R = \text{rated } V_{RRM}$ | $I_G = 0$ | $T_C = 110^\circ\text{C}$ | | | 2 | mA |
| I_{GT} | Gate trigger current | $V_{AA} = 12\text{ V}$ | $R_L = 100\ \Omega$ | $t_{p(g)} \geq 20\ \mu\text{s}$ | | 8 | 20 | mA |
| V_{GT} | Gate trigger voltage | $V_{AA} = 12\text{ V}$ | $R_L = 100\ \Omega$ | $T_C = -40^\circ\text{C}$ | | | 2.5 | V |
| | | $V_{AA} = 12\text{ V}$ | $R_L = 100\ \Omega$ | | | 0.8 | 1.5 | |
| | | $V_{AA} = 12\text{ V}$ | $R_L = 100\ \Omega$ | $T_C = 110^\circ\text{C}$ | 0.2 | | | |
| I_H | Holding current | $V_{AA} = 12\text{ V}$ | | $T_C = -40^\circ\text{C}$ | | | 100 | mA |
| | | Initiating $I_T = 100\text{ mA}$ | | | | | 40 | |
| V_T | On-state voltage | $I_T = 8\text{ A}$ | (see Note 5) | | | | 1.7 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_D = \text{rated } V_D$ | $I_G = 0$ | $T_C = 110^\circ\text{C}$ | | 400 | | V/ μs |

NOTE 5: This parameter must be measured using pulse techniques, $t_p = 300\ \mu\text{s}$, duty cycle $\leq 2\%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|-----------------|---|-----|-----|------|---------------------------|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 3 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | $^\circ\text{C}/\text{W}$ |

PRODUCT INFORMATION

THERMAL INFORMATION

**AVERAGE ON-STATE CURRENT
DERATING CURVE**

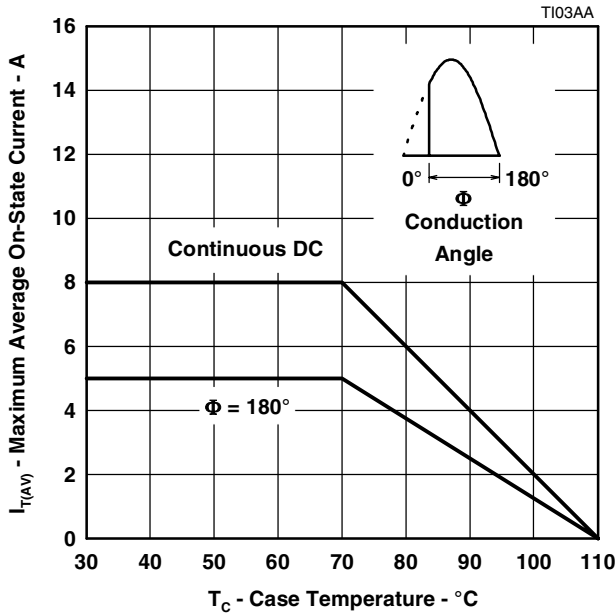


Figure 1.

**MAX ANODE POWER LOSS
VS
ON-STATE CURRENT**

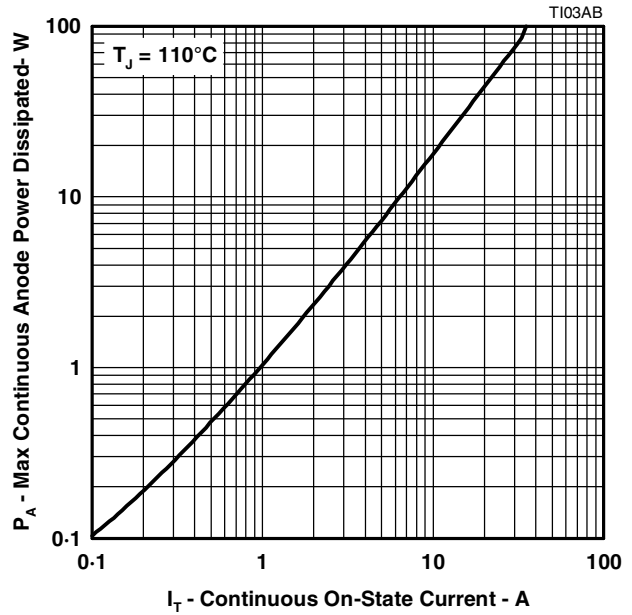


Figure 2.

**SURGE ON-STATE CURRENT
VS
CYCLES OF CURRENT DURATION**

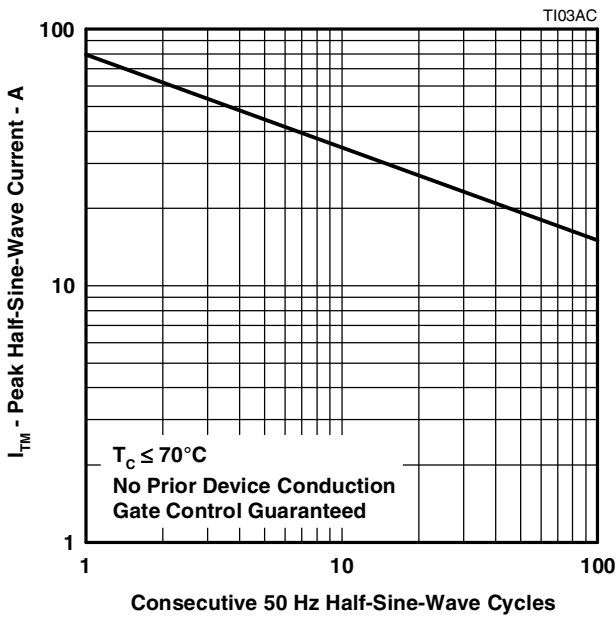


Figure 3.

**TRANSIENT THERMAL RESISTANCE
VS
CYCLES OF CURRENT DURATION**

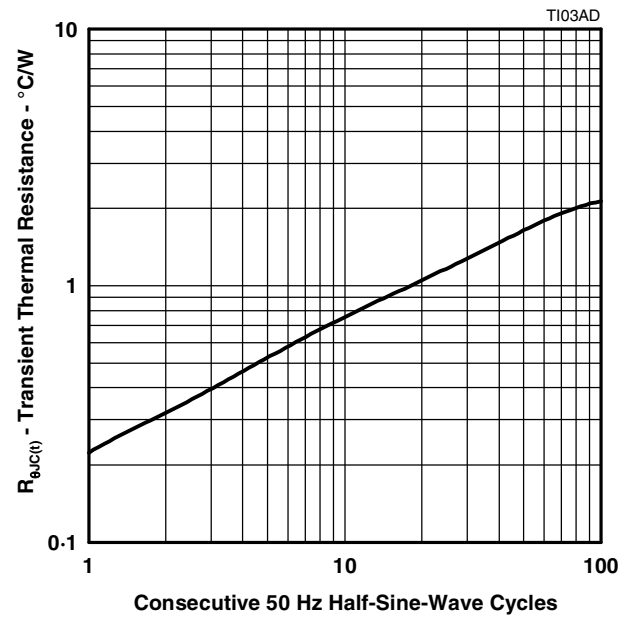


Figure 4.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT
vs
CASE TEMPERATURE

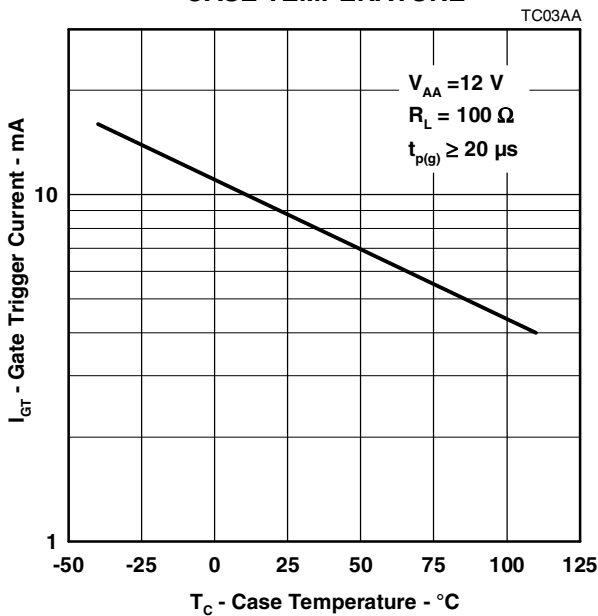


Figure 5.

GATE TRIGGER VOLTAGE
vs
CASE TEMPERATURE

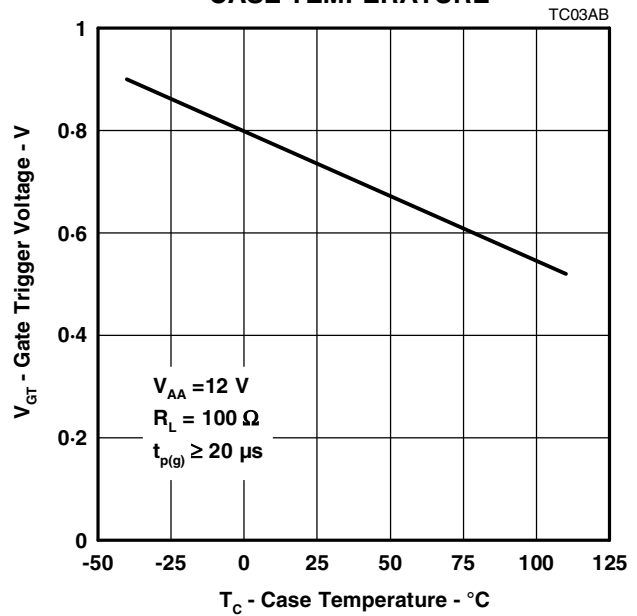


Figure 6.

HOLDING CURRENT
vs
CASE TEMPERATURE

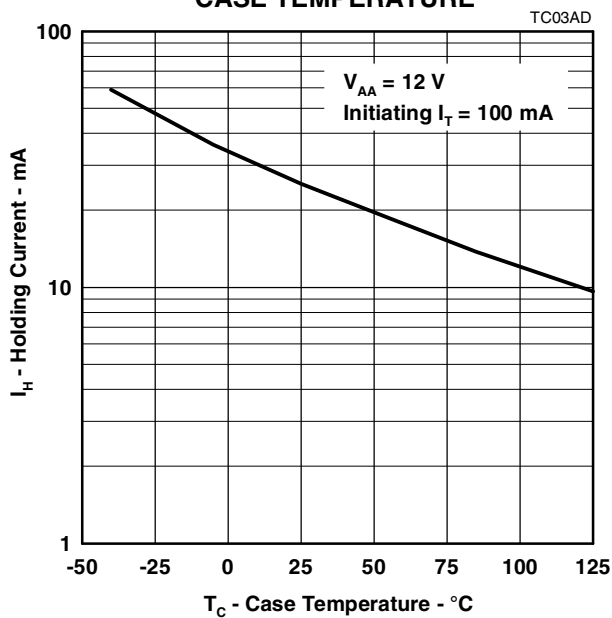


Figure 7.

PEAK ON-STATE VOLTAGE
vs
PEAK ON-STATE CURRENT

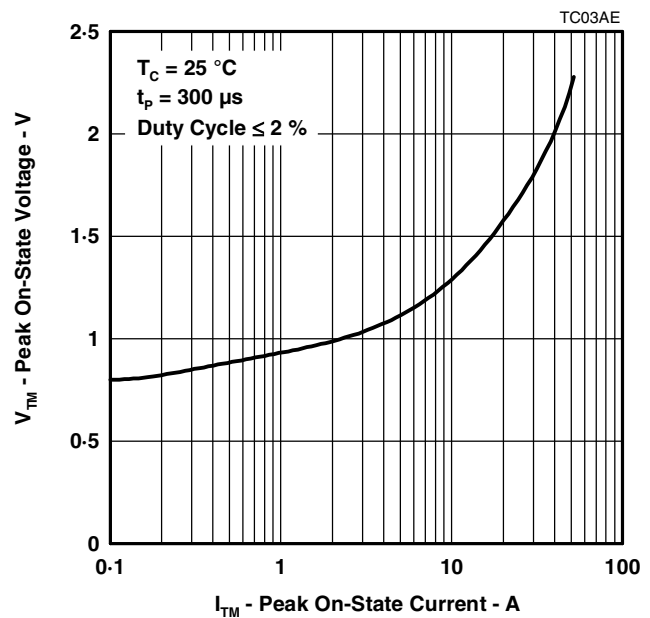


Figure 8.

PRODUCT INFORMATION

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